

LG L-2800

SERVICE MANUAL

1. Equalizer Amp. Section

Adopted is an Operational I.C., RAYTHEON RC-4558-DN, which is of 8-pin Dual Inline Package Type. A built-in phase compensation capacitor for high frequency makes it impossible to adjust the value according to R & D purpose. This contributes so much to the various characteristics and sonic quality. Fundamentally, at the negative feedback amplifier, especially the equalizer amplifier, the high frequency phase compensation should be kept in proper condition. When the compensation is too weak, the circuit becomes unstable and in many case oscillation is inevitable. In such state, the sonic quality is out of discussion.

On the contrary, the phase compensation is too strong, the distortion at high frequency range is much increased and at the same time it affects sonic quality to a great extent. That is the input impedance is reduced by the high frequency phase compensation (e.g., Mirror Integration), which is indispensable to the multi-stage amplifier, and linearity of the former stage is affected to deteriorate the distortion characteristic. The capacitor inserted between Q6 and Q7 is for high frequency compensation.

To comply with the unique gain distribution of the L2800, we considered a semi-conductor device which offers more inherent gain, comparing with the conventional 3-stage E-E feedback type equalizer. The I.C. offers more than 100dB of inherent gain, and the loop gain at 1KHz is approximately 37dB, which ensures sufficient amount of Negative Feedback at low frequency range. The RC-4558-DN is carefully selected to fulfill no more than 1.5uV Input-Conversion Noise Voltage. Despite that the phase compensation is included, proper compensation is realized as well as the stability, and therefore any type of cartridge can be connected. As for the load condition, the I.C. circuitry exceeds the conventional 3-stage E-E feedback Circuitry.

2. Power Amp Section

Adopted is the fully complementary circuit configuration, which seems to be the most ideal one at present. Signals are supplied from the equalizer amp directly to the power amp section via buffer stage. The rated output of 50W/ch is realized at 190mV of equalizer output voltage (Input Sensitivity 2.8mV). That is the voltage gain is approximate 39dB which is higher by some 6dB than that of standard power amplifiers. And naturally various problems must be considered.

First, referring the harmonic distortion, especially at high frequency range, it tends to be worse. In actual, distortion at 10KHz is twice as bad as that of the amplifier having some 33dB voltage gain. This is of course in the case of using the same semi-conductor device.

To compensate the lost gain caused by applying Negative Feedback, it is necessary to increase the inherent gain by delving into the inherent characteristics. At the first differential input stage, it is of utmost necessity to reduce the DC offset voltage at the output terminal, and of high hfe at the operational current area. For the L2800, adopted is the one of 3dB allowance between minimum and maximum. The standard hfe value is 500, which is very high. Also at this stage a zener diode is arranged to deal with the mains power fluctuation.

Second Differential Amp. Stage.

This stage plays an important role to decide distortion ratio, especially at high frequency range. Fundamentally transistors of high f_T and low C_{ob} are necessary, and high load impedance should be realized since the stage makes most of the voltage gain. Therefore inherent gain is obtained sufficiently up to high frequency range thanks to constant current drive.

The f_T of the transistors is over 130MHz ($I_c = 10mA$), and the C_{ob} is less than 2pF, which is far above the audio frequency band, nevertheless from the view point of f_{ae} , the f_{ea} is 75KHz in case h_{fe} is determined as 200. Thus such high frequency characteristic is indispensable.

Also at the driver stage and the power stage, transistors of high f_T are necessary when good high frequency characteristic is required, but there exists close relation between f_T and breakdown of transistors: When f_T is extended, high frequency becomes unstable, and power transistors are easily damaged due to oscillation etc. And recently, this is solved by increasing $V_{CE(sat.)}$, the saturation voltage between collector and emitter, which deteriorates voltage utilization ratio as well as linearity of h_{fe} at the time of huge current driving.

The power transistors adopted in the L2800 realized excellent reliability against breakdown by using larger scale pellet than that of the conventional transistors. Adopting larger scale pellet in the power transistors, the L2800 realized excellent reliability against breakdown without deteriorating high frequency characteristic. Of course the linearity of h_{fe} is excellent.

Thus delving into the semi-conductor device, we increased the loop gain, and the high frequency characteristic is far much improved. This is because the high frequency compensation could be slighter based on the betterment of the inherent characteristics.

3. Tone Control Section

Adopted is the NF type with turnover frequency selector of two steps both for bass and treble respectively.

Bass Turnover Frequency:	150Hz,	300Hz
Treble Turnover Frequency:	3KHz,	6KHz

4. Delay Time Muting Section

In the amplifier of Direct-Coupled configuration, the speaker loads are directly connected to the power transistors, therefore it may be possible to damage the speaker systems in case DC potential appears at the output terminal. Also a slight DC potential gives some bias to the speakers, which affects the sonic quality. Thus the protection circuit is indispensable to eliminate these situation. For the L2800, the Delay Time Muting Circuit operates as a protection circuit at the same time. Therefore the amplifier is muted 5 - 10 seconds at the time of turning the power switch on.

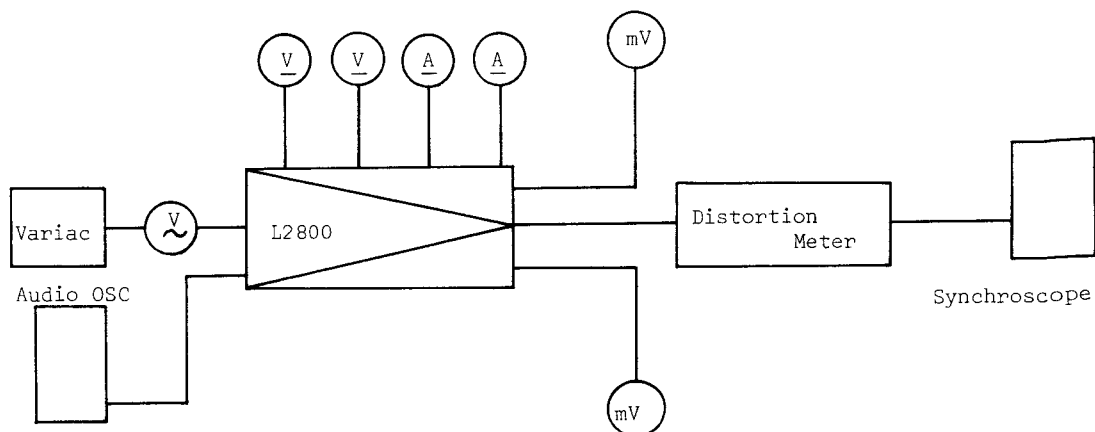
5. Peak Indicator Circuit (PB-1067)

The output signal meets the Peak Detection circuit composed of Q801, Q802, D802 and C802, whose detected DC signal is then converted into low-impedance by current booster Q803 and Q804.

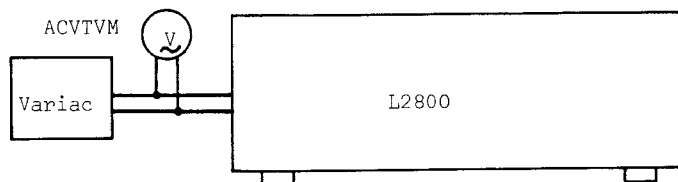
Of course different threshold level is arranged for each L.E.D. driver Q505 - Q510 to make them light up in accordance with the signal level.

Measurement Instruments & Tools

- | | |
|---------------------------|---------------------------------|
| 1) AC Voltmeter (ACVTVM) | 7) Synchroscope |
| 2) Milivoltmeter | 8) 8-ohm Non-Induction Resistor |
| 3) DC Ammeter | 9) Frequency Counter |
| 4) DC Voltmeter (DCVTVM) | 10) Small \ominus driver |
| 5) Audio Oscillator (AFO) | 11) Short Pin-Plug |
| 6) Distortion Meter | 12) Variac |



Voltage Check & Delay Time Muting

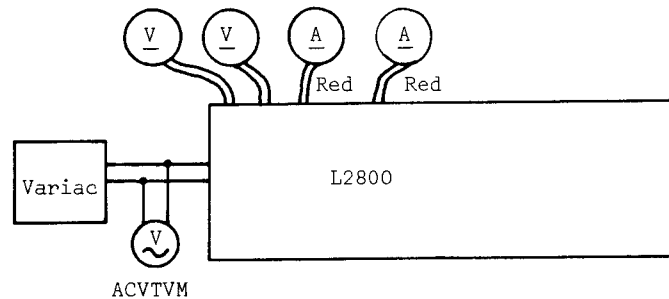


1. Connect a Variac to the amplifier.
2. Adjust the Variac to obtain "0 V" reading.
3. Confirm the 5A fuse is inserted in the fuse holder placed between the power transformer and the back panel.
4. Set the power switch to "ON".
5. Gradually increase the voltage of the variac, confirming there is no trouble, until the precise AC mains voltage is obtained. Also note that the pilot lamp lights up.
6. Check the voltage at each terminal on PB-891.

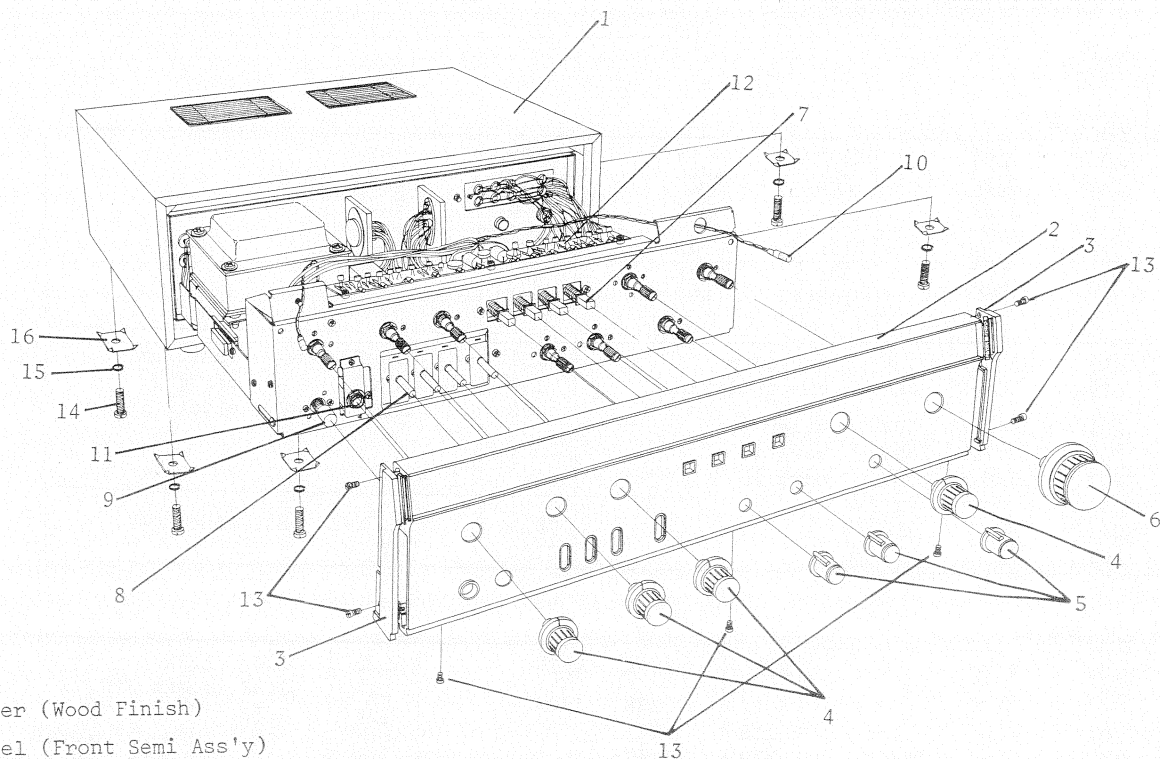
P-107	DC	+	around 40V against chassis
P-108		-	" 40V "
P-709		+	" 20V "
P-203		+	" 15V "
P-204		-	" 15V "

7. Check precise AC mains voltage is available at the two AC outlets on the back panel.
8. Shut off the power switch.
9. Check precise AC line voltage is available only at the extra AC outlet (UN SWITCHED).
10. Set the power switch to "ON" again to check the operation of the delay time muting circuit. Muting time: 6 secs (+4, -1).

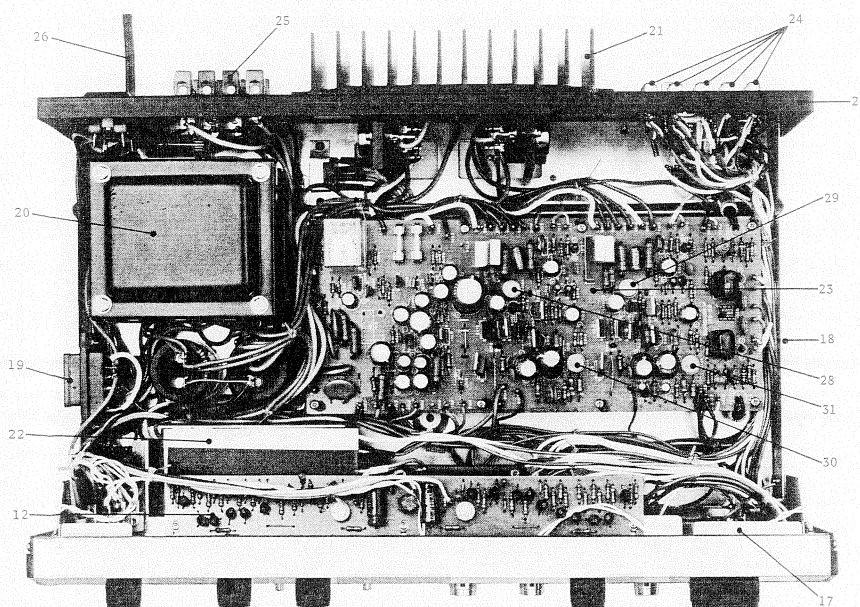
IDLE ADJUST & ZERO DC OFFSET



1. Set the power switch to "OFF".
2. Set both of the VR101 (for Idle Adjust) on PB-891 to the extreme counter-clockwise position.
3. Set both of the VR102 (for Zero DC offset) at the mechanical center position.
4. Remove the Red lead wire from the heatsink. Connect the DC ammeter (100mA); \oplus to the lead wire and \ominus to the socket on the heatsink.
5. Connect the DC voltmeter (less than 1V at full scale) to the speaker terminals to measure DC offset. The speaker switch should be at the "main & remote" position.
6. Press the power switch to "ON"
7. After one minute, adjust VR-101 to obtain 30mA reading on the DC ammeter. (This should be applied on both channels.)
8. Adjust VR-102 to obtain 0 DC offset. (This should also be applied on both channels.)
9. Power switch to OFF.
10. All the wiring should be reset as they were.



1. Cover (Wood Finish)
2. Panel (Front Semi Ass'y)
3. Side Plate
4. Knob (Function, Treble, Bass, SP Selector)
5. Knob (Balance, Monitor, Dubbing)
6. Main Volume Knob
7. Push SW. Knob
8. Lever SW. Knob
9. Power SW. Knob
10. Edge Lamp
11. Headphone Jack
12. L.E.D. PCB Ass'y
13. Screw 3mm ϕ x 6
14. Screw 4mm ϕ x 20
15. Spring Washer 4mm ϕ
16. Square Washer (with Toothed Lock)



17. Sub Panel
18. Main Chasses Complete Ass'y
19. Voltage Selector (100-120-220-240V)
20. Power Transformer
21. Power Amp. Complete Ass'y
22. Shield Plate
23. PB-891 (Pre, Main P.C.B.)
24. Pin Jack Ass'y
25. Speaker Terminal
26. Main Cord
27. Back Panel
28. VR102 (0 DC offset-Lch)
29. VR102 (0 DC offset-Rch)
30. VR101 (Idling-Lch)
31. VR101 (Idling-Rch)

L2800 REPLACEMENT PARTS LIST

PB-891

SECTION A

R201	120K	R207	1K	R104	47
202	3.3K	208	680	105	6.8K 1/2W
203	390K	209	220K	106	6.8K 1/2W
204	620	R101	1M	107	47K
205	39K	102	4.7K	R110	8.2K
206	560K	103	47	R115	470
C201	2.2uF 16V	tantalum		C101	10uF 16V tantalum
202	22uF 16V	electrolytic		102	0.0022uF ceramic
205	0.47uF 50V	mylar		103	100uF 16V electrolytic
206	0.047uF 50V	ceramic			
207	0.047uF 50V	ceramic			
Q201	IC	RE4558		VR101	4.7K-B semi-fixed pot.
101	TR	2SA750		D101	WZ120

SECTION B

R108	3.3K	R115	1.5K 1/2W	R122	100 1/2W
109	3.3K	R117	33K 1/2W	123	0.33 cement MPC 71
R101	180	118	22	124	0.33 " "
112	68 1/2W	119	3.9K	125	22 1/2W J metal
113	47K	120	1.2K	126	47 1W J "
114	430	121	100 1/2W		
C104	100uF 50V	electrolytic		C110	0.023uF 50V mylar
105	47pF	ceramic		111	470uF 6.3V electrolytic
106	47pF	ceramic		112	1uF 50V electrolytic
107	100uF 16V	electrolytic		C114	1uF 50V electrolytic
108	100uF 50V	electrolytic		C116	0.1uF mylar
109	0.0015uF	ceramic			
Q102	2SA750	Q106	2SC945	D102	VD1221
103	2SC1507	106	2SB536	103	VD1221
104	2SC1507	108	2SD381	VR102	4.7K-B
105	2SC945			L101	2uH L02

SECTION C

R101	1M	R110	8.2K	R119	3.9K
102	4.7K	111	180K	120	180
103	47	112	68 1/2W	121	100 1/2W
104	47	113	47K	122	100 1/2W
105	6.8K 1/2W	114	430	123	0.33 cement MPC 71
106	6.8K 1/2W	115	470	124	0.33 " "
107	47K	115	1.5K 1/2W	125	22 1/2W J metal
108	3.3K	R117	33K 1/2W	126	47 1W J metal
109	3.3K	118	22		
C101	10uF 16V	tantalum		C109	0.0015uF ceramic
102	0.0022uF	ceramic		110	0.0022uF 50V mylar
103	100uF 16V	electrolytic		111	470uF 6.3V electrolytic
104	100uF 50V	electrolytic		113	0.047uF YZ ceramic
105	47pF	ceramic		115	0.047uF YZ ceramic
106	47pF	ceramic		116	0.1uF K mylar
107	100uF 16V	electrolytic			
108	100uF 50V	electrolytic			
Q101	2SA750	D101	WZ120	VR101	4.7K-B
102	2SA750	102	VD1221	102	4.7K-B
103	2SC1507	103	VD1221	L101	2uH L02
104	2SC1507				
105	2SC945				
106	2SC945				

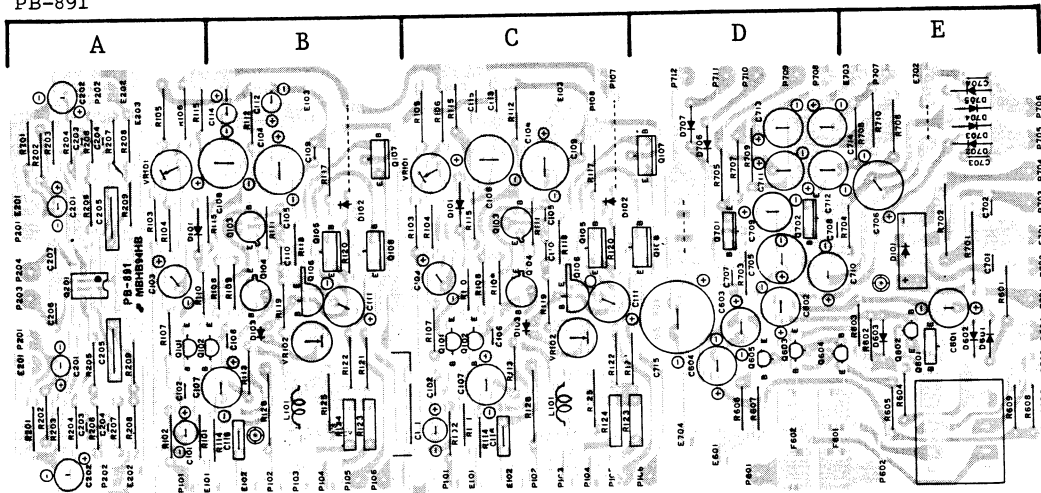
SECTION D

R606 607	3.9K 2.7K	R703 705	27K 1.2K 1/2W	R707 709	1.8K 1/2W 4.7K 1/2W J metalized
C602 603 604	220uF 10V 220uF 10V 220uF 10V	electrolytic electrolytic electrolytic	C710 711 712 713 714 715	100uF 35V 47uF 25V 47uF 25V 100uF 25V 100uF 25V 2200uF 16V	electrolytic electrolytic electrolytic electrolytic electrolytic electrolytic
C705 C707 708 709	220uF 35V 100pF 100pF 100uF 35V	electrolytic ceramic ceramic electrolytic			
Q107 108 603	2SB536 2SD381 2SA733	Q604 605 701	2SC945 2SC945 2SD571	Q702 D707	2SB605 1N4002

SECTION E

R601 602 603 604 605	100 1/2W 56K 1K 10K 10K	R608 609 701 702 704	18K 18K 4.7K 3W J metalized 4.7K 3W J metalized 27K	R706 708 710	3.3K 1/2W 1.8K 1/2W 4.7K 1/2W metalized
C601 701 702	22uF 50V 0.01uF 250V 0.01uF 250V	electrolytic ceramic ceramic	C703 704 706	0.01uF 250V 0.01uF 250V 220uF 35V	ceramic ceramic electrolytic
D601 602 603	1N4002 1N4002 1S1555	D702 703 704	1N4002 1N4002 1N4002	D705 Q601 602	1N4002 2SD571 2SC945

PB-891



FILTER SWITCH PCB

Resistor	3.3K 2 pcs 12K 2 pcs	Capacitor	0.082uF K mylar 1 pc
Push Switch	SPZ 045A01		0.15uF K mylar 2 pcs 0.033uF K mylar 2 pcs 0.0047uF K mylar 2 pcs

LEVER SWITCH PCB

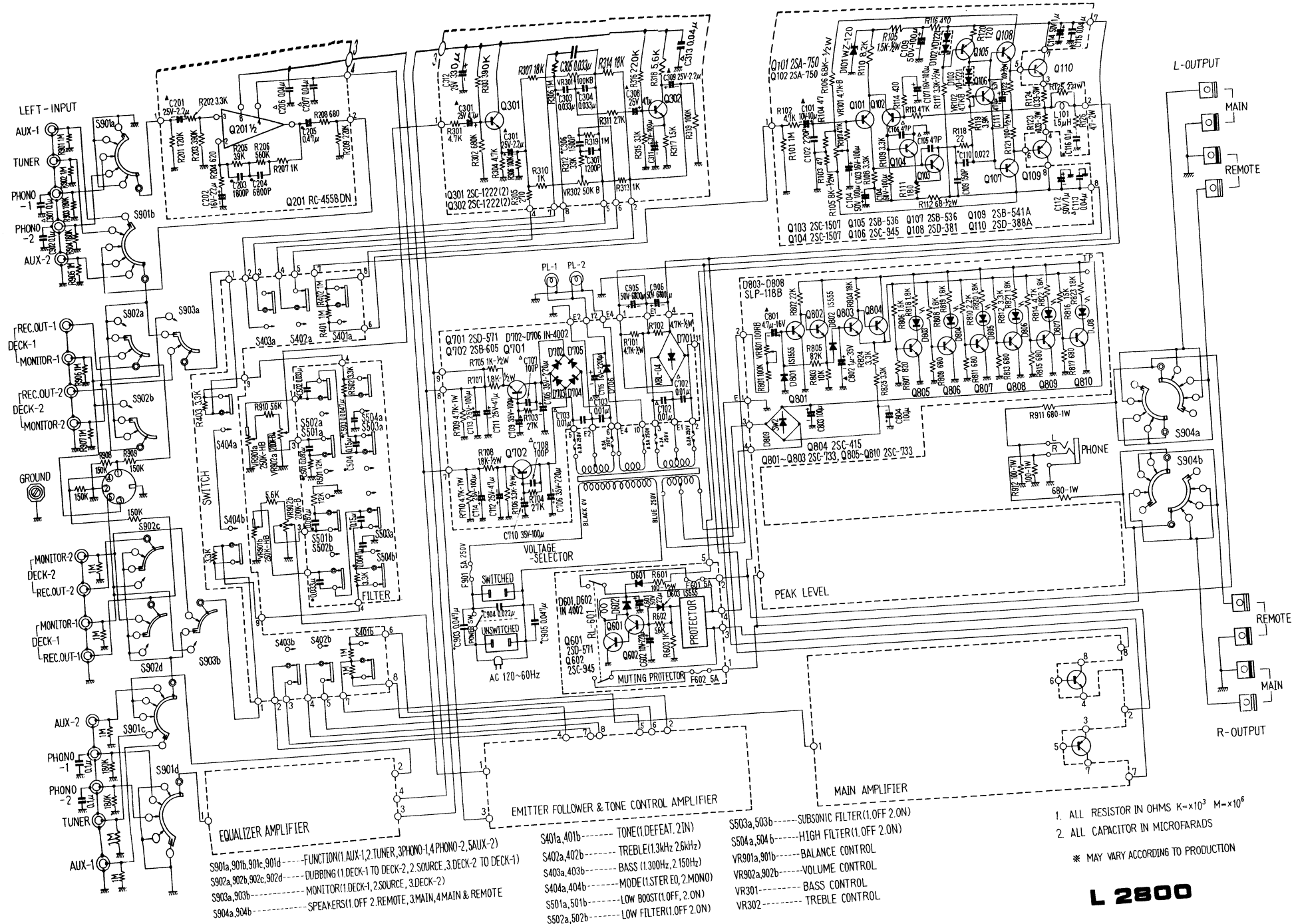
Lever Switch	SLA32204	3 pcs	Resistor	3.3K	2 pcs
	SLA32205	1 pc		1M	4 pcs

TONE CONTROL PCB

Resistor	100K	4	pcs	Resistor	680K	1	pc			
	1.5K	2			3.3K	2				
	5.6K	2			1M	4				
	4.7K	4			18K	4				
	390K	2			2.7K	2				
	1K	4			68K	1				
	220K	2			10K	1				
	270	2			33K	1				
Capacitor	2.2uF	25V	tantalum	4	pcs	Capacitor	0.012uF	mylar	2	pcs
	4.7uF	25V	tantalum	4			0.015uF	mylar	2	
	100uF	6.3V	electrolytic	2			0.33	mylar	6	
	330uF	25V	electrolytic	1			0.47uF	ceramic	1	YZ
Transistor	2SC1222	4	pcs							

PEAK INDICATOR PCB

R801	100K	2 pcs	R810	2.2K	2 pcs	R819	1.8K	2 pcs
802	22K	2	811	680	2	820	1.8K	2
803	10K	2	812	3.3K	2	821	1.8K	2
804	180K	2	813	680	2	822	1.8K	2
805	82K	2	814	4.7K	2	823	1.8K	2
806	1.5K	2	815	680	2	824	3.3K	2
807	820	2	816	15K	2	825	3.3K	2
808	1.8K	2	817	680	2			
809	680	2	818	1.8K	2			
Q801 - Q803		2SC733	6 pcs	C801	4.7uF 100V tantalum	2 pcs		
Q804		2SA495	2	802	1uF 35V tantalum	2		
Q805 - Q810		2SC733	12	803	100uF 35V electrolytic	1		
				804	100uF 35V electrolytic	1		
D809	W02 7532	1 pc	VR801	semifixed pot	100K-B	2 pcs		
801	1S1555	2 pcs						
802	1S1555	2 pcs						
803-8	L.E.D.	12 pcs						



1. ALL RESISTOR IN OHMS K= $\times 10^3$ M= $\times 10^6$
 2. ALL CAPACITOR IN MICROFARADS
- * MAY VARY ACCORDING TO PRODUCTION

L 2800